

U.S.S.N. 10/662,845

22. (Original) The method of claim 13, further comprising forming a layer of polysilicon over the high dielectric constant metal oxide layer according to a CVD process carried out between about 100 milliTorr and about 760 Torr.

23. (Original) The method of claim 22 wherein the CVD process comprises a silane gas precursor and at least one of a nitrogen and hydrogen carrier gas.

24.-32. (Cancelled)

REMARKS

Applicants hereby elect without traverse the prosecution of Group II, method claims 1-23. Non-elected claims 24-32 have been cancelled and withdrawn from further consideration by the Examiner.

Respectfully submitted,

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